

Features

- Fast Read Access Time - 150 ns
- Automatic Page Write Operation
Internal Address and Data Latches for 64 Bytes
- Fast Write Cycle Times
Page Write Cycle Time: 2 ms maximum
1 to 64 Byte Page Write Operation
- Low Power Dissipation
60 mA Active Current
100 μ A CMOS Standby Current
- Hardware and Software Data Protection
- DATA Polling and Toggle Bit for End of Write Detection
- High Reliability CMOS Technology
Endurance: 100,000 Cycles
Data Retention: 10 years
- Single 5 V \pm 10% Supply
- CMOS and TTL Compatible Inputs and Outputs
- JEDEC Approved Byte-Wide Pinout
- Full Military, Commercial, and Industrial Temperature Ranges

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**64K (8K x 8)
CMOS
E²PROM with
Software Data
Protection**

Description

The AT28C64B is a high-performance Electrically Erasable and Programmable Read Only Memory. Its 64K of memory is organized as 8,192 words by 8 bits. Manufactured with Atmel's advanced nonvolatile CMOS technology, the device offers access times to 150 ns with power dissipation of just 440 mW. When the device is deselected, the CMOS standby current is less than 100 μ A.

The AT28C64B is accessed like a Static RAM for the read or write cycle without the need for external components. The device contains a 64-byte page register to allow writing of up to 64 bytes simultaneously. During a write cycle, the addresses and 1 to 64 bytes of data are inter-

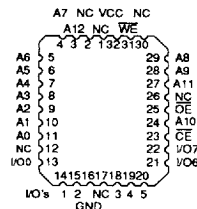
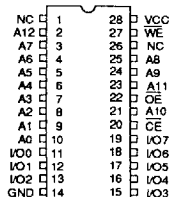
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Pin Configurations

TSOP Top View



Pin Name	Function
A0 - A12	Addresses
CE	Chip Enable
OE	Output Enable
WE	Write Enable
I/O0 - I/O7	Data Inputs/Outputs
NC	No Connect



Note: PLCC package pins 1 and 17 are DON'T CONNECT.

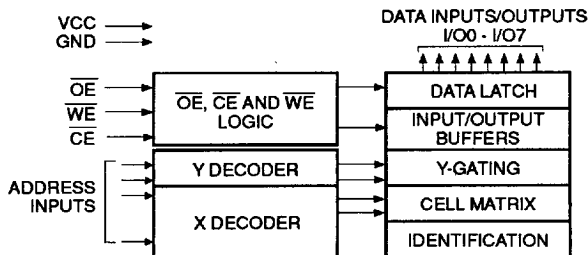


Description (Continued)

nally latched, freeing the address and data bus for other operations. Following the initiation of a write cycle, the device will automatically write the latched data using an internal control timer. The end of a write cycle can be detected by DATA polling of I/O7. Once the end of a write cycle has been detected a new access for a read or write can begin.

Atmel's 28C64B has additional features to ensure high quality and manufacturability. The device utilizes internal error correction for extended endurance and improved data retention characteristics. An optional software data protection mechanism is available to guard against inadvertent writes. The device also includes an extra 64 bytes of E²PROM for device identification or tracking.

Block Diagram



Absolute Maximum Ratings*

Temperature Under Bias.....	-55°C to +125°C
Storage Temperature.....	-65°C to +150°C
All Input Voltages (including N.C. Pins) with Respect to Ground	-0.6 V to +6.25 V
All Output Voltages with Respect to Ground	-0.6 V to V _{CC} +0.6 V
Voltage on \overline{OE} and A9 with Respect to Ground	-0.6 V to +13.5 V

*NOTICE: Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Device Operation

READ: The AT28C64B is accessed like a Static RAM. When \overline{CE} and \overline{OE} are low and \overline{WE} is high, the data stored at the memory location determined by the address pins is asserted on the outputs. The outputs are put in the high-impedance state when either \overline{CE} or \overline{OE} is high. This dual line control gives designers flexibility in preventing bus contention in their system.

BYTE WRITE: A low pulse on the \overline{WE} or \overline{CE} input with \overline{CE} or \overline{WE} low (respectively) and \overline{OE} high initiates a write cycle. The address is latched on the falling edge of \overline{CE} or \overline{WE} , whichever occurs last. The data is latched by the first rising edge of \overline{CE} or \overline{WE} . Once a byte write has been started it will automatically time itself to completion.

PAGE WRITE: The page write operation of the AT28C64B allows one to 64 bytes of data to be written into the device during a single internal programming period. A page write operation is initiated in the same manner as a byte write; after the first byte is written, it can then be followed by one to 63 additional bytes. Each successive byte must be loaded within 150 μ s (tBLC) of the previous byte. If the tBLC limit is exceeded the AT28C64B will cease accepting data and commence the internal programming operation. All bytes during a page write operation must reside on the same page as defined by the state of the A6-A12 inputs. For each \overline{WE} high to low transition during the page write operation, A6 - A12 must be the same.

The A0 to A5 inputs are used to specify which bytes within the page are to be written. The bytes may be loaded in any order and may be altered within the same load period. Only bytes which are specified for writing will be written; unnecessary cycling of other bytes within the page does not occur.

DATA POLLING: The AT28C64B features \overline{DATA} Polling to indicate the end of a write cycle. During a byte or page write cycle an attempted read of the last byte written will result in the complement of the written data to be presented on I/O7. Once the write cycle has been completed, true data is valid on all outputs, and the next write cycle may begin. \overline{DATA} Polling may begin at anytime during the write cycle.

TOGGLE BIT: In addition to \overline{DATA} Polling the AT28C64B provides another method for determining the end of a write cycle. During the write operation, successive attempts to read data from the device will result in I/O6 toggling between one and zero. Once the write has completed, I/O6 will stop toggling and valid data will be read. Reading the toggle bit may begin at any time during the write cycle.

DATA PROTECTION: If precautions are not taken, inadvertent writes may occur during transitions of the host system power

supply. Atmel has incorporated both hardware and software features that will protect the memory against inadvertent writes.

HARDWARE PROTECTION: Hardware features protect against inadvertent writes to the AT28C64B in the following ways: (a) VCC sense - if VCC is below 3.8 V (typical) the write function is inhibited; (b) VCC power-on delay - once VCC has reached 3.8 V the device will automatically time out 5 ms (typical) before allowing a write; (c) write inhibit - holding any one of \overline{OE} low, \overline{CE} high or \overline{WE} high inhibits write cycles; (d) noise filter - pulses of less than 15 ns (typical) on the \overline{WE} or \overline{CE} inputs will not initiate a write cycle.

SOFTWARE DATA PROTECTION: A software controlled data protection feature has been implemented on the AT28C64B. When enabled, the software data protection (SDP), will prevent inadvertent writes. The SDP feature may be enabled or disabled by the user; the AT28C64B is shipped from Atmel with SDP disabled.

SDP is enabled by the user issuing a series of three write commands; three specific bytes of data are written to three specific addresses (refer to Software Data Protection Algorithm). After writing the three-byte command sequence and twc the entire AT28C64B will be protected against inadvertent writes. It should be noted that once protected the user may still perform a byte or page write to the AT28C64B. This is done by preceding the data to be written by the same three-byte command sequence used to enable SDP.

Once set, SDP will remain active unless the disable command sequence is issued. Power transitions do not disable SDP and SDP will protect the AT28C64B during power-up and power-down conditions. All command sequences must conform to the page write timing specifications. The data in the enable and disable command sequences is not actually written into the device; their addresses may still be written with user data in either a byte or page write operation.

After setting SDP, any attempt to write to the device without the three-byte command sequence will start the internal write timers. No data will be written to the device; however, for the duration of twc, read operations will effectively be polling operations.

DEVICE IDENTIFICATION: An extra 64 bytes of E²PROM memory are available to the user for device identification. By raising A9 to 12 V ± 0.5 V and using address locations 1FC0H to 1FFFH the additional bytes may be written to or read from in the same manner as the regular memory array.

Pin Capacitance (f = 1 MHz, T = 25°C) ⁽¹⁾

	Typ	Max	Units	Conditions
C _{IN}	4	6	pF	V _{IN} = 0 V
C _{OUT}	8	12	pF	V _{OUT} = 0 V

Note: 1. This parameter is characterized and is not 100% tested.



D.C. and A.C. Operating Range

		AT28C64B-15	AT28C64B-20	AT28C64B-25
Operating Temperature (Case)	Com.	0°C - 70°C	0°C - 70°C	0°C - 70°C
	Ind.	-40°C - 85°C	-40°C - 85°C	-40°C - 85°C
	Mil.	-55°C - 125°C	-55°C - 125°C	-55°C - 125°C
V _{CC} Power Supply		5 V ± 10%	5 V ± 10%	5 V ± 10%

Operating Modes

Mode	\overline{CE}	\overline{OE}	\overline{WE}	I/O
Read	V _{IL}	V _{IL}	V _{IH}	DOUT
Write ⁽²⁾	V _{IL}	V _{IH}	V _{IL}	DIN
Standby/Write Inhibit	V _{IH}	X ⁽¹⁾	X	High Z
Write Inhibit	X	X	V _{IH}	
Write Inhibit	X	V _{IL}	X	
Output Disable	X	V _{IH}	X	High Z
Chip Erase	V _{IL}	V _H ⁽³⁾	V _{IL}	High Z

Notes: 1. X can be V_{IL} or V_{IH}.

2. Refer to A.C. Programming Waveforms.

3. V_H = 12.0 V ± 0.5 V.

D.C. Characteristics

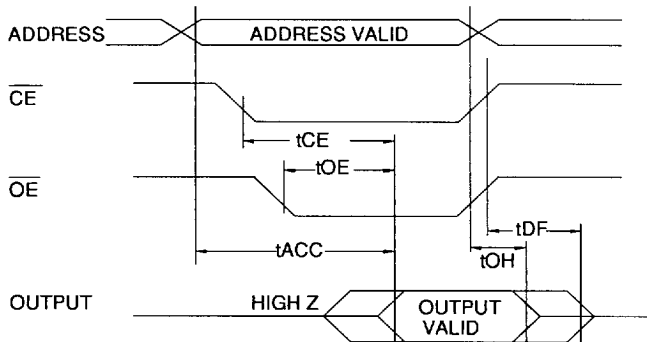
Symbol	Parameter	Condition	Min	Max	Units
I _{LI}	Input Load Current	V _{IN} = 0 V to V _{CC} + 1 V		10	μA
I _{LO}	Output Leakage Current	V _{I/O} = 0 V to V _{CC}		10	μA
I _{SB1}	V _{CC} Standby Current CMOS	\overline{CE} = V _{CC} - 0.3 V to V _{CC} + 1 V	Com., Ind.	100	μA
			Mil.	200	μA
I _{SB2}	V _{CC} Standby Current TTL	\overline{CE} = 2.0 V to V _{CC} + 1 V		2	mA
I _{CC}	V _{CC} Active Current	f = 5 MHz; I _{OUT} = 0 mA		60	mA
V _{IL}	Input Low Voltage			0.8	V
V _{IH}	Input High Voltage		2.0		V
V _{OL}	Output Low Voltage	I _{OL} = 2.1 mA		.40	V
V _{OH}	Output High Voltage	I _{OH} = -400 μA	2.4		V

A.C. Read Characteristics

Symbol	Parameter	AT28C64B-15		AT28C64B-20		AT28C64B-25		Units
		Min	Max	Min	Max	Min	Max	
t_{ACC}	Address to Output Delay		150		200		250	ns
$t_{CE}^{(1)}$	\overline{CE} to Output Delay		150		200		250	ns
$t_{OE}^{(2)}$	\overline{OE} to Output Delay	0	70	0	80	0	100	ns
$t_{DF}^{(3,4)}$	\overline{CE} or \overline{OE} to Output Float	0	50	0	55	0	60	ns
t_{OH}	Output Hold from \overline{OE} , \overline{CE} or Address, whichever occurred first	0		0		0		ns

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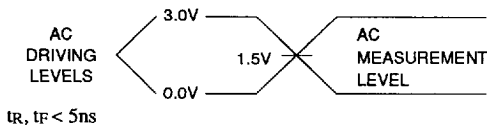
A.C. Read Waveforms



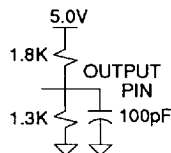
Notes:

- \overline{CE} may be delayed up to $t_{ACC} - t_{CE}$ after the address transition without impact on t_{ACC} .
- \overline{OE} may be delayed up to $t_{CE} - t_{OE}$ after the falling edge of \overline{CE} without impact on t_{CE} or by $t_{ACC} - t_{OE}$ after an address change without impact on t_{ACC} .
- t_{DF} is specified from \overline{OE} or \overline{CE} whichever occurs first ($C_L = 5 \text{ pF}$).
- This parameter is characterized and is not 100% tested.

Input Test Waveforms and Measurement Level



Output Test Load

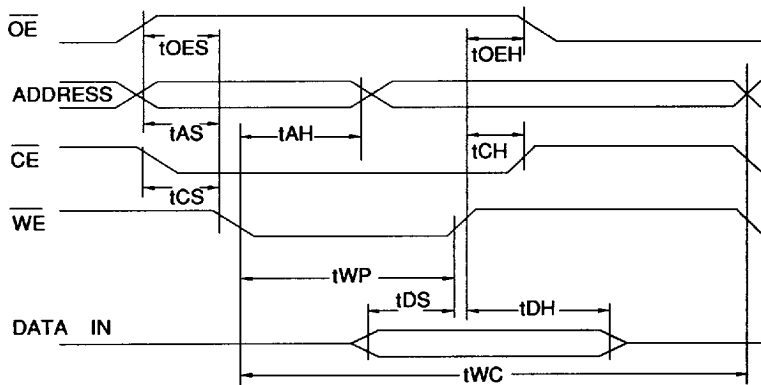


A.C. Write Characteristics

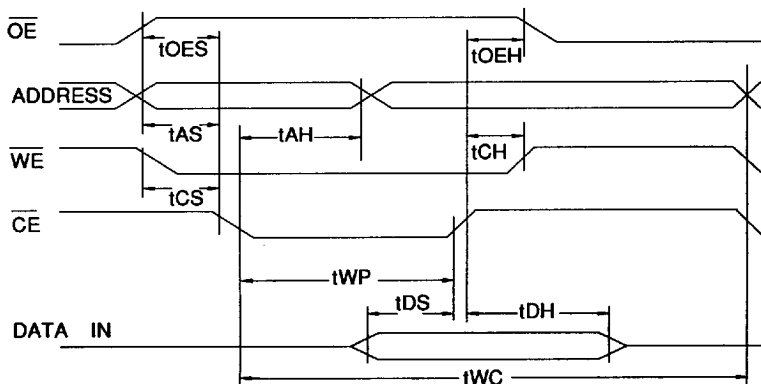
Symbol	Parameter	Min	Max	Units
tAS, tOES	Address, \overline{OE} Set-up Time	0		ns
tAH	Address Hold Time	50		ns
tCS	Chip Select Set-up Time	0		ns
tCH	Chip Select Hold Time	0		ns
tWP	Write Pulse Width (\overline{WE} or \overline{CE})	100		ns
tDS	Data Set-up Time	50		ns
tDH,tOEH	Data, \overline{OE} Hold Time	0		ns
tWC	Write Cycle Time	AT28C256		2ms

Note: 1. NR = No Restriction

A.C. Write Waveforms- \overline{WE} Controlled



A.C. Write Waveforms- \overline{CE} Controlled

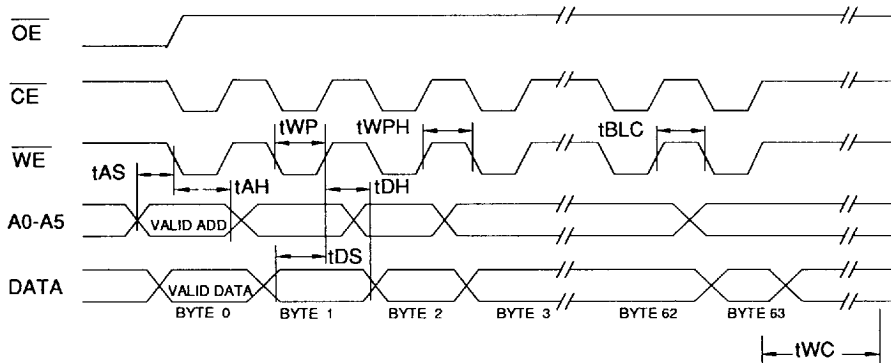


Page Mode Characteristics

Symbol	Parameter	MIn	Max	Units
tWC	Write Cycle Time AT28C256		2	ms
tAS	Address Set-up Time	0		ns
tAH	Address Hold Time	50		ns
tDS	Data Set-up Time	50		ns
tDH	Data Hold Time	0		ns
tWP	Write Pulse Width	100		ns
tBLC	Byte Load Cycle Time		150	μs
tWPH	Write Pulse Width High	50		ns

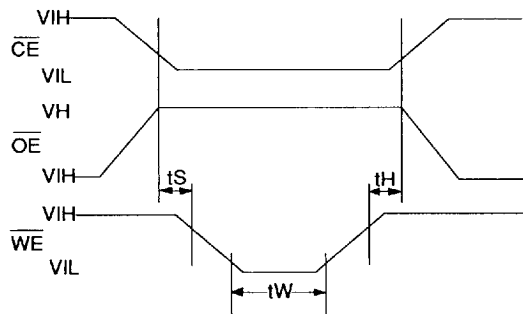
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Page Mode Write Waveforms



Notes: A6 through A12 must specify the same page address during each high to low transition of \overline{WE} (or \overline{CE}).
 \overline{OE} must be high only when \overline{WE} and \overline{CE} are both low.

Chip Erase Waveforms



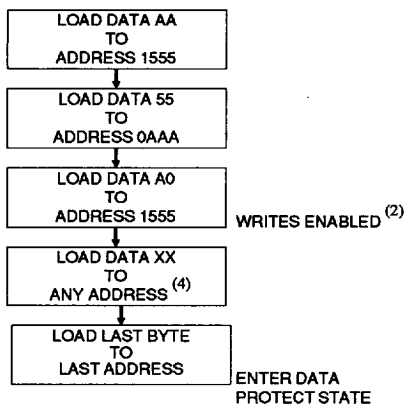
$t_S = t_H = 5 \mu\text{sec (min.)}$
 $t_W = 10 \text{ msec (min.)}$
 $V_H = 12.0 \text{ V} \pm 0.5 \text{ V}$



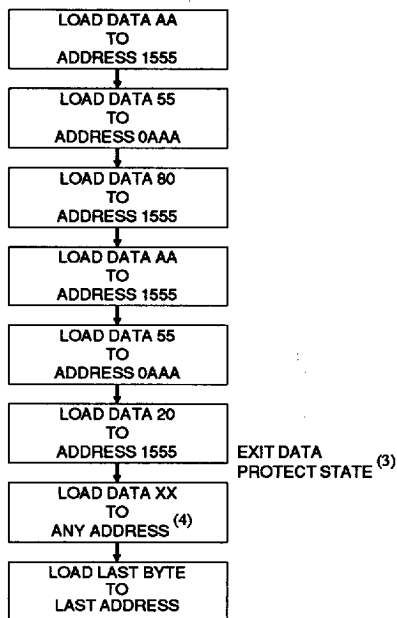
2-129

1074177 0005074 162

Software Data Protection Enable Algorithm ⁽¹⁾



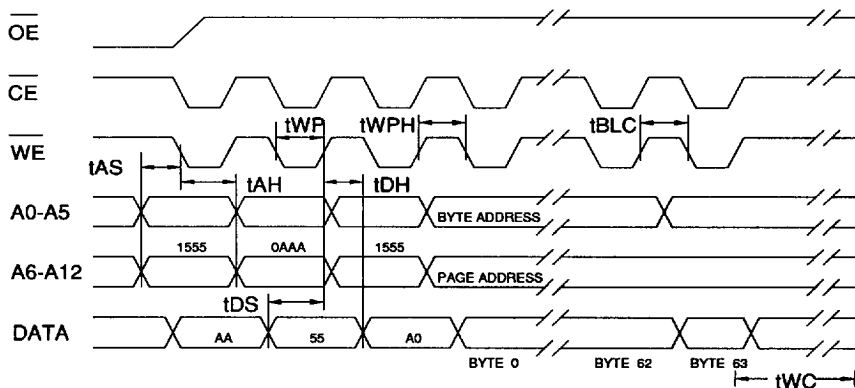
Software Data Protection Disable Algorithm ⁽¹⁾



Notes for software program code:

1. Data Format: I/O7 - I/O0 (Hex); Address Format: A12 - A0 (Hex).
2. Write Protect state will be activated at end of write even if no other data is loaded.
3. Write Protect state will be deactivated at end of write period even if no other data is loaded.
4. 1 to 64 bytes of data are loaded.

Software Protected Write Cycle Waveforms



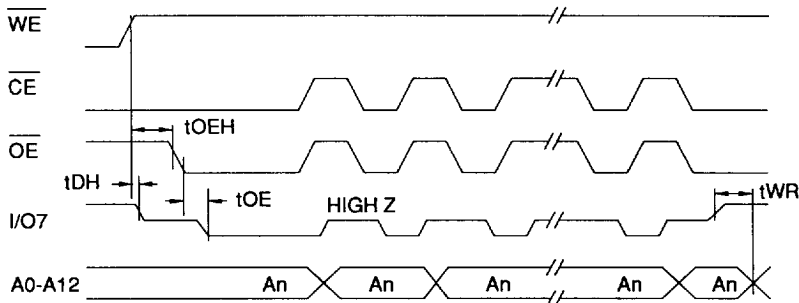
- Notes:
- A6 through A12 must specify the same page address during each high to low transition of \overline{WE} (or \overline{CE}) after the software code has been entered.
 - \overline{OE} must be high only when \overline{WE} and \overline{CE} are both low.

Data Polling Characteristics⁽¹⁾

Symbol	Parameter	Min	Typ	Max	Units
t _{DH}	Data Hold Time	0			ns
t _{OE}	$\overline{\text{OE}}$ Hold Time	0			ns
t _{OE}	$\overline{\text{OE}}$ to Output Delay			100	ns
t _{WR}	Write Recovery Time	0			ns

Note: 1. These parameters are characterized and not 100% tested.

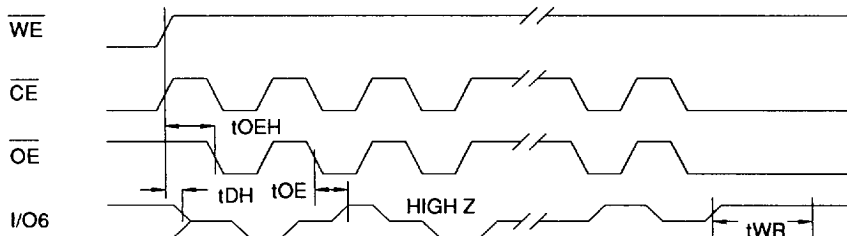
Data Polling Waveforms

Toggle Bit Characteristics⁽¹⁾

Symbol	Parameter	Min	Typ	Max	Units
t _{DH}	Data Hold Time	10			ns
t _{OE}	$\overline{\text{OE}}$ Hold Time	10			ns
t _{OE}	$\overline{\text{OE}}$ to Output Delay			100	ns
t _{OEHP}	$\overline{\text{OE}}$ High Pulse	150			ns
t _{WR}	Write Recovery Time	0			ns

Note: 1. These parameters are characterized and not 100% tested.

Toggle Bit Waveforms

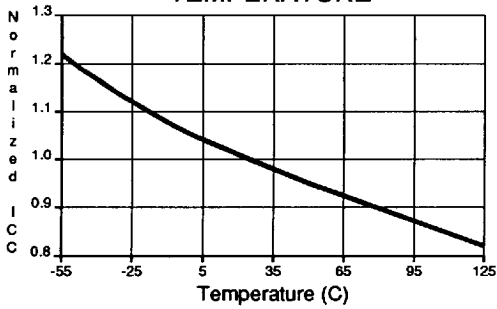


Notes:

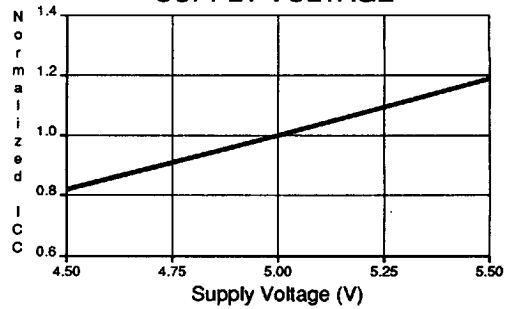
1. Toggling either $\overline{\text{OE}}$ or $\overline{\text{CE}}$ or both $\overline{\text{OE}}$ and $\overline{\text{CE}}$ will operate toggle bit.
2. Beginning and ending state of I/O6 will vary.
3. Any address location may be used but the address should not vary.



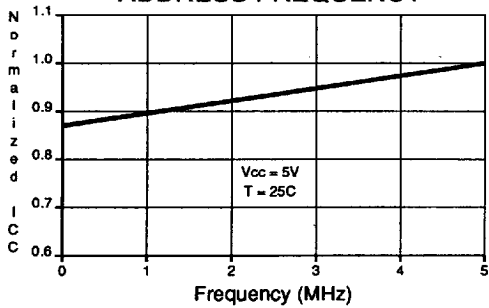
**NORMALIZED SUPPLY CURRENT vs.
TEMPERATURE**



**NORMALIZED SUPPLY CURRENT vs.
SUPPLY VOLTAGE**



**NORMALIZED SUPPLY CURRENT vs.
ADDRESS FREQUENCY**



Ordering Information

t _{acc} (ns)	I _{cc} (mA)		Ordering Code	Package	Operation Range
	Active	Standby			
150	60	0.1	AT28C64B-15DC AT28C64B-15JC AT28C64B-15PC AT28C64B-15SC AT28C64B-15TC	28D6 32J 28P6 28S 28T	Commercial (0°C to 70°C)
			AT28C64B-15DI AT28C64B-15JI AT28C64B-15PI AT28C64B-15SI AT28C64B-15TI	28D6 32J 28P6 28S 28T	Industrial (-40°C to 85°C)
150	80	0.2	AT28C64B-15DM/883 AT28C64B-15UM/883	28D6 28U	Military/883C Class B, Fully Compliant (-55°C to 125°C)
200	60	0.1	AT28C64B-20DC AT28C64B-20JC AT28C64B-20PC AT28C64B-20SC AT28C64B-20TC	28D6 32J 28P6 28S 28T	Commercial (0°C to 70°C)
			AT28C64B-20DI AT28C64B-20JI AT28C64B-20PI AT28C64B-20SI AT28C64B-20TI	28D6 32J 28P6 28S 28T	Industrial (-40°C to 85°C)
200	80	0.2	AT28C64B-20DM/883 AT28C64B-20UM/883	28D6 28U	Military/883C Class B, Fully Compliant (-55°C to 125°C)
250	60	0.1	AT28C64B-25DC AT28C64B-25JC AT28C64B-25PC AT28C64B-25SC AT28C64B-25TC	28D6 32J 28P6 28S 28T	Commercial (0°C to 70°C)
			AT28C64B-25DI AT28C64B-25JI AT28C64B-25PI AT28C64B-25SI AT28C64B-25TI	28D6 32J 28P6 28S 28T	Industrial (-40°C to 85°C)
250	80	0.2	AT28C64B-25DM/883 AT28C64B-25UM/883	28D6 28U	Military/883C Class B, Fully Compliant (-55°C to 125°C)

Package Type

28D6	28 Lead, 0.600" Wide, Non-Windowed Ceramic Dual Inline Package (Cerdip)
32J	32 Lead, Plastic J-Leaded Chip Carrier (PLCC)
28P6	28 Lead, 0.600" Wide, Plastic Dual Inline Package (PDIP)
28S	28 Lead, 0.300" Wide, Plastic Gull Wing Small Outline (SOIC)
28T	28 Lead, Plastic Thin Small Outline Package (TSOP)
28U	28 Pin, Ceramic Pin Grid Array (PGA)

